Paula Diaz Reigosa

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9487409/publications.pdf

Version: 2024-02-01

30 papers	578 citations	840776 11 h-index	839539 18 g-index
30 all docs	30 docs citations	30 times ranked	507 citing authors

#	Article	IF	Citations
1	Short-circuit robustness of retrograde channel doping 1.2ÂkV SiC MOSFETs. Microelectronics Reliability, 2021, 120, 114117.	1.7	4
2	Switching Stability Analysis of Paralleled RC-IGBTs With Snapback Effect. IEEE Transactions on Electron Devices, 2021, 68, 3429-3434.	3.0	6
3	Impact of Repetitive Short-Circuit Tests on the Normal Operation of SiC MOSFETs Considering Case Temperature Influence. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2020, 8, 195-205.	5.4	31
4	Effects of the HV-BIGT Design Elements on the High-Frequency Oscillation Instability during Short Circuit Transients. , 2019, , .		0
5	Modeling of IGBT With High Bipolar Gain for Mitigating Gate Voltage Oscillations During Short Circuit. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2019, 7, 1584-1592.	5.4	4
6	Implications of short-circuit events on power cycling of 1.2-kV/20-A SiC MOSFET power modules. Microelectronics Reliability, 2019, 100-101, 113373.	1.7	4
7	Impact of the Case Temperature on the Reliability of SiC MOSFETs Under Repetitive Short Circuit Tests. , 2019, , .		8
8	Implications of Ageing Through Power Cycling on the Short-Circuit Robustness of 1.2-kV SiC mosfets. IEEE Transactions on Power Electronics, 2019, 34, 11182-11190.	7.9	22
9	Improving the Short-Circuit Reliability in IGBTs: How to Mitigate Oscillations. IEEE Transactions on Power Electronics, 2018, 33, 5603-5612.	7.9	17
10	Increasing emitter efficiency in 3.3-kV enhanced trench IGBTs for higher short-circuit capability. , 2018, , .		5
11	Investigation on the degradation indicators of short-circuit tests in 1.2â€¯kV SiC MOSFET power modules. Microelectronics Reliability, 2018, 88-90, 661-665.	1.7	11
12	Effect of short-circuit stress on the degradation of the SiO2 dielectric in SiC power MOSFETs. Microelectronics Reliability, 2018, 88-90, 577-583.	1.7	35
13	Non-uniform Temperature Distribution Implications on Thermal Analysis Accuracy of Si IGBTs and SiC MOSFETs. , 2018, , .		3
14	On-line solder layer degradation measurement for SiC-MOSFET modules under accelerated power cycling condition. Microelectronics Reliability, 2018, 88-90, 563-567.	1.7	17
15	Impact of meteorological variations on the lifetime of grid-connected PV inverters. Microelectronics Reliability, 2018, 88-90, 1019-1024.	1.7	8
16	Failure Analysis of a Degraded 1.2 kV SiC MOSFET after Short Circuit at High Temperature. , 2018, , .		7
17	Capacitive effects in IGBTs limiting their reliability under short circuit. Microelectronics Reliability, 2017, 76-77, 485-489.	1.7	4
18	A survey of SiC power MOSFETs short-circuit robustness and failure mode analysis. Microelectronics Reliability, 2017, 76-77, 272-276.	1.7	68

#	Article	IF	Citations
19	A Short-Circuit Safe Operation Area Identification Criterion for SiC MOSFET Power Modules. IEEE Transactions on Industry Applications, 2017, 53, 2880-2887.	4.9	78
20	Compact electro-thermal modeling of a SiC MOSFET power module under short-circuit conditions. , 2017, , .		7
21	TCAD analysis of short-circuit oscillations in IGBTs. , 2017, , .		5
22	Approaching repetitive short circuit tests on MW-scale power modules by means of an automatic testing setup. , 2016, , .		0
23	Investigation on the short circuit safe operation area of SiC MOSFET power modules. , 2016, , .		6
24	New layout concepts in MW-scale IGBT modules for higher robustness during normal and abnormal operations. , 2016, , .		8
25	Modern IGBT gate driving methods for enhancing reliability of high-power converters â€" An overview. Microelectronics Reliability, 2016, 58, 141-150.	1.7	25
26	A humidity-dependent lifetime derating factor for DC film capacitors. , 2015, , .		27
27	Prediction of Bond Wire Fatigue of IGBTs in a PV Inverter under a Long-Term Operation. IEEE Transactions on Power Electronics, 2015, , 1-1.	7.9	128
28	Robustness of MW-Level IGBT modules against gate oscillations under short circuit events. Microelectronics Reliability, 2015, 55, 1950-1955.	1.7	20
29	Study on Oscillations During Short Circuit of MW-Scale IGBT Power Modules by Means of a 6-kA/1.1-kV Nondestructive Testing System. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2015, 3, 756-765.	5.4	17
30	Tvindkraft: Implementing a 500 kW 21-IGBT-based frequency converter for a 1.7 MW wind power conversion system. , 2013, , .		3